ABSTRACT

A semiconductor memory device and a method of manufacturing the semiconductor memory device are provided. The semiconductor memory device includes a plurality of insulating layers spaced apart from each other in a stacking direction, a slit insulating layer passing through the plurality of insulating layers, a plurality of first variable resistance layers alternately disposed with the plurality of insulating layers in the stacking direction, a plurality of conductive lines interposed between the slit insulating layer and the plurality of first variable resistance layers and alternately disposed with the plurality of insulating layers in the stacking direction, a conductive pillar passing through the plurality of insulating layers and the plurality of first variable resistance layers, and a second variable resistance layer surrounding a sidewall of the conductive pillar.

FIG. 3